

base material for the production of electric circuitboards,
preferably an Aramid-reinforced resin.

8. (Amended) A circuitboard according to claim 1,
characterized in that the thin glass layers (11, 17) have a
thickness of less than or equal to 1.1 mm and are made of a
borosilicate glass.

9. (Amended) A circuitboard according to claim 1,
characterized in that the thin glass layers (11, 17) and the
carrier plates (10, 16) are glued or pressed together.

10. (Amended) A circuitboard according to claim 1,
characterized in that at least individual layers of the thin
glass layers (11, 17) are designed as continuous layers.

11. (Amended) A circuitboard according to claim 1,
characterized in that at least individual layers of the thin
glass layers (11, 17) are structured so as to form individual
optical conductors (13) within the layer, separated from one
another by interspaces (12).

13. (Amended) A circuitboard according to claim 11,
characterized in that the interspaces (12) between the optical
conductors (13) are filled with a filling material (14, 18).

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14. (Amended) A circuitboard according to claim 1, characterized in that coupling openings (26, 28) are provided for optical coupling of optically active elements (25, 27) arranged on the top and or bottom sides of the circuitboard (30), so that the concealed thin glass layer(s) (11, 17) or optical conductors (13) located in an optical conduction level (OL) are accessible from the outside through these coupling openings.

15. (Amended) A method of producing a circuitboard according to claim 1, characterized in that in a first step at least one thin glass layer (11, 17) is joined over the entire area to at least one carrier plate (10, 16) to form an optical sandwich (15; 15.1, ..., 15.3), and in a second step, the optical sandwich (15; 15.1, ..., 15.3) is connected to the circuitboard (30) as an optical conduction level (OL) having one or more electrical conduction levels (EL) in a stack arrangement.

17. (Amended) A method according to claim 15, characterized in that the thin glass layer (11, 17) joined to the carrier plate (10, 16) is structured between the first and second steps.

20. (Amended) A method according to claim 17, characterized in that the free surface area of the structured thin glass layer (11) is coated with a reflective layer (29), preferably made of a metal, by vapor deposition, galvanic or chemical deposition.

21. (Amended) A method according to claim 17,
characterized in that the interspaces (12) in the structured
thin glass layer (11, 17) are filled with a filling material
(14, 18) having a refractive index lower than the refractive
index of the glass of the thin glass layer (11, 17).

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